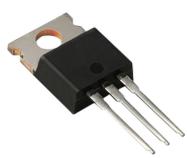
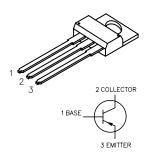
# **Bipolar Transistor**

### RoHS Compliant



### **Description:**

Silicon, TO-220, Plastic, PNP Power Transistor Designed for use in general purpose amplifier and switching applications



#### Features:

- High Current Gain Bandwidth Product fτ 10MHz (Min.) @ Ic 500mA
- Collector Emitter Sustaining Voltage VCEO 70V (Min.)

### **Absolute Maximum Ratings:**

Characteristic	Symbol	Rating
Collector - Base Voltage	Vсво	80V
Collector - Emitter Voltage	Vceo	70V
Emitter - Base Voltage	Vebo	5V
Continuous Collector Current	lc	7A
Base Current	Ів	3A
Total Device Dissipation (Tc = +25°C), Derate above 25°C	Po	40W 0.32mW/°C
Operating Junction Temperature Range	TJ	-65°C to +150°C
Storage Temperature Range	Тѕтс	-65°C to +150°C

#### Electrical Characteristics (TA = 25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Max.	Unit				
OFF Characteristics									
Collector - Emitter Breakdown Voltage (Note 1)		Ic = 100mA, I <sub>B</sub> = 0	70	-	V				
Collector Cut-off Current	ICEX	$V_{CE} = 80V, V_{BE(off)} = 1.5V$	-	100	μA				
	ICEO	V <sub>CB</sub> = 60V, I <sub>B</sub> = 0	-	1	mA				
Emitter Cut-off Current	Іево	VEB = 5V, IC = 0	-	1	mA				
ON Characteristics									
DC Current Cain Nate 1	bee	Vce = 4V, Ic = 2A	30	150	-				
DC Current Gain, Note 1	hfe	Vce = 4V, Ic = 7A	2.3	-	-				

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# **Bipolar Transistor**

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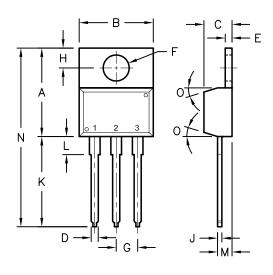
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Parameter	Symbol	Test Conditions	Min.	Max.	Unit
Collector - Emitter Saturation Voltage	VCE(sat)	Ic = 7A, IB = 3A	-	3.5	V
Base - Emitter On Voltage	VBE(on)	Ic = 7A, Vce = 4V	-	3	V
Small-Signal Characteristics					
Current Gain - Bandwidth Product	fτ	Vce = 10V, Ic = 0.5A, f = 1MHz	3	-	MHz
Output Capacitance	Cobo	Vсв = 10V, IE = 0, f = 0.1MHz	-	250	pF

hfe

Note 1: Pulse Test : Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%

Note 2: fr is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity



Small-Signal Current Gain

#### **Pin Configuration:**

- 1. Base
- 2. Collector
- 3. Emitter

Dim.	Α	В	С	D	Е	F	G	Н	J	К	L	М	N	0
Min.	14.42	9.63	3.65	-	1.15	3.75	2.29	2.54	-	12.7	2.8	2.03	-	7∘
Max.	16.51	10.67	4.83	0.9	1.4	3.88	2.79	3.43	0.56	14.73	4.07	2.92	31.24	<i>'</i>

Dimensions : Millimetres

### Part Number Table

Vce = 4V, Ic = 0.5A, f = 50kHz

Description	Part Number			
Bipolar Transistor, PNP, 7A, 70V, TO-220	2N6107			

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